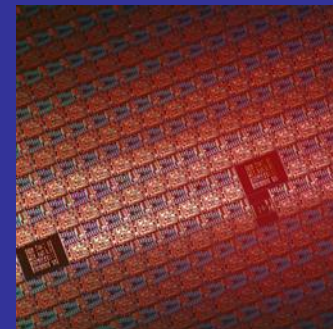




Accelerating the next technology revolution

February 2013 Resist TWG

Karen Petrillo
Serge Tedesco



SEMATECH

Housekeeping



- Welcome to the IEUVI Resist TWG meeting
- Please sign in
- Please pick up your name tag. If one doesn't exist, please use one of the blank tags, and add your name and the company you work for
- At the end of the meeting, please return the name tags
- We would like this to be an interactive meeting. Please feel free to ask questions and make suggestions.
- All meeting presentations will be made available on the IEUVI web site after the meeting

Introduction

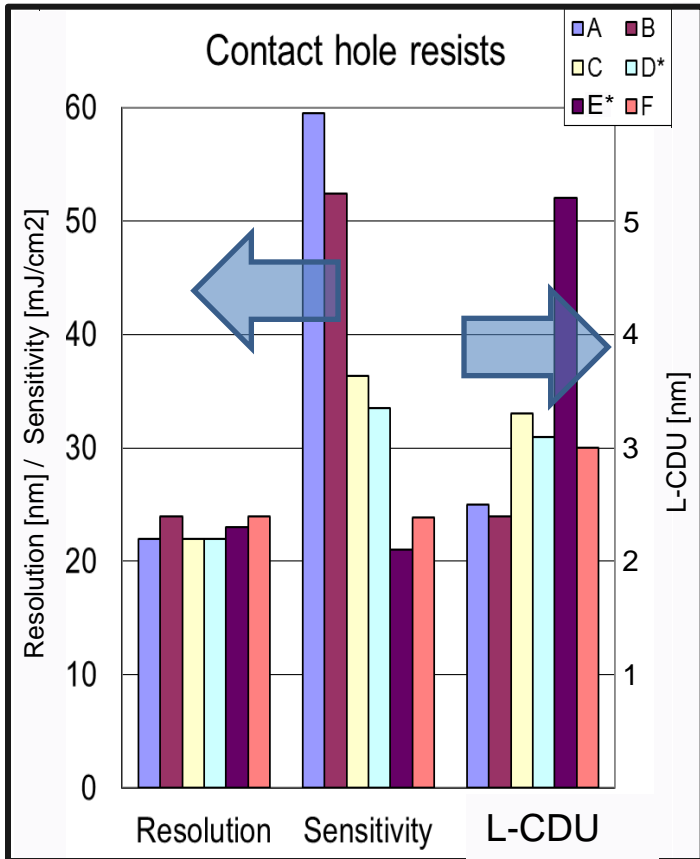


- **Resolution and Sensitivity are improving**
 - Resist vendors are now demonstrating **15 - 16nm hp** resolution with CAR on all EUV Micro Exposure Tools
 - Preliminary results from the NXE3300 are starting to become available
- **LWR and pattern collapse need improvement**
 - Current materials are have not met the LWR target
 - Many materials at ~3nm, target is <2nm
 - LWR improvement belongs to both litho and pattern transfer
 - Looking for an integrated solution to get to the target level
- **Contact hole imaging is becoming a focus item**
 - Materials showing resolution in the 22 – 24nm hp range
 - Improving Local CDU is very important
 - Trends show L-CDU improves as sensitivity decreases
- **Outgassing**
 - Major issue limiting materials research and development
 - Testing availability is improving
 - Ability to research topics related to outgassing is becoming available
- **Interest in DSA as a means to compliment traditional lithography**

Contact hole imaging on the LBNL MET tool



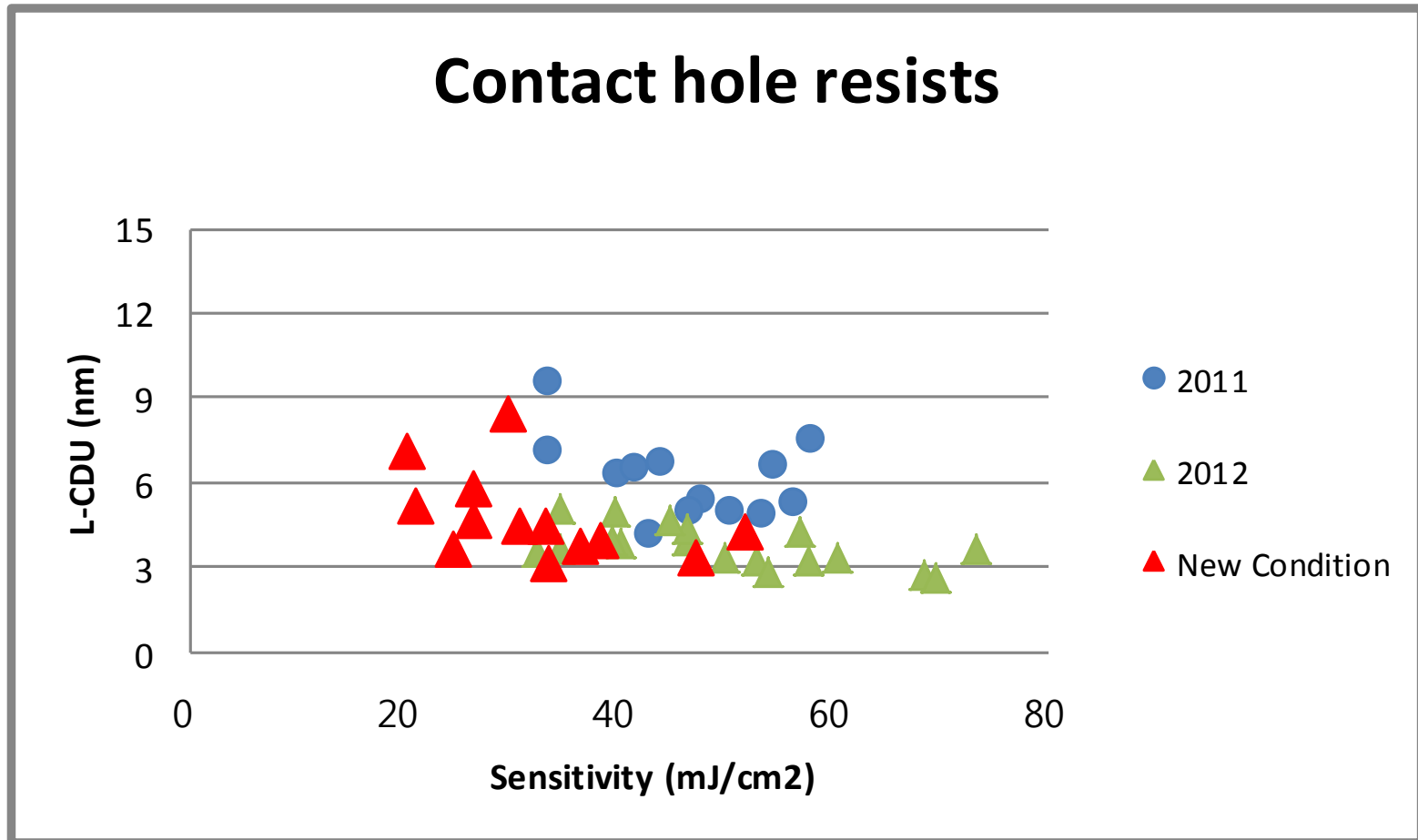
Berkeley MET
 Quad, NA 0.3, sigma 0.48~0.68
 FT 80nm, * 60nm
 Underlayers
 No mask bias, * (+20% Bias)



* L-CDU was measured at 26 or 25nm HP

	26nm	24nm	23nm	22nm	21nm	20nm
A	59.5mJ/cm ² 2.5nm					
B	52.4mJ/cm ² 2.4nm					
C	36.3mJ/cm ² 3.3nm					
D*	33.5mJ/cm ² 3.1nm (25nmHP)					
E*	21.0mJ/cm ² 5.2nm (25nmHP)					
F	23.9mJ/cm ² 3.0nm					
						Sensitivity [mJ/cm ²] / L-CDU [nm]

Contact hole resist progress and trends



Trend shows improved L-CDU at the expense of sensitivity

Line/Space Performance



Best materials from each supplier

BMET, PseudoPSM
FT 30nm, 35nm
Underlayers

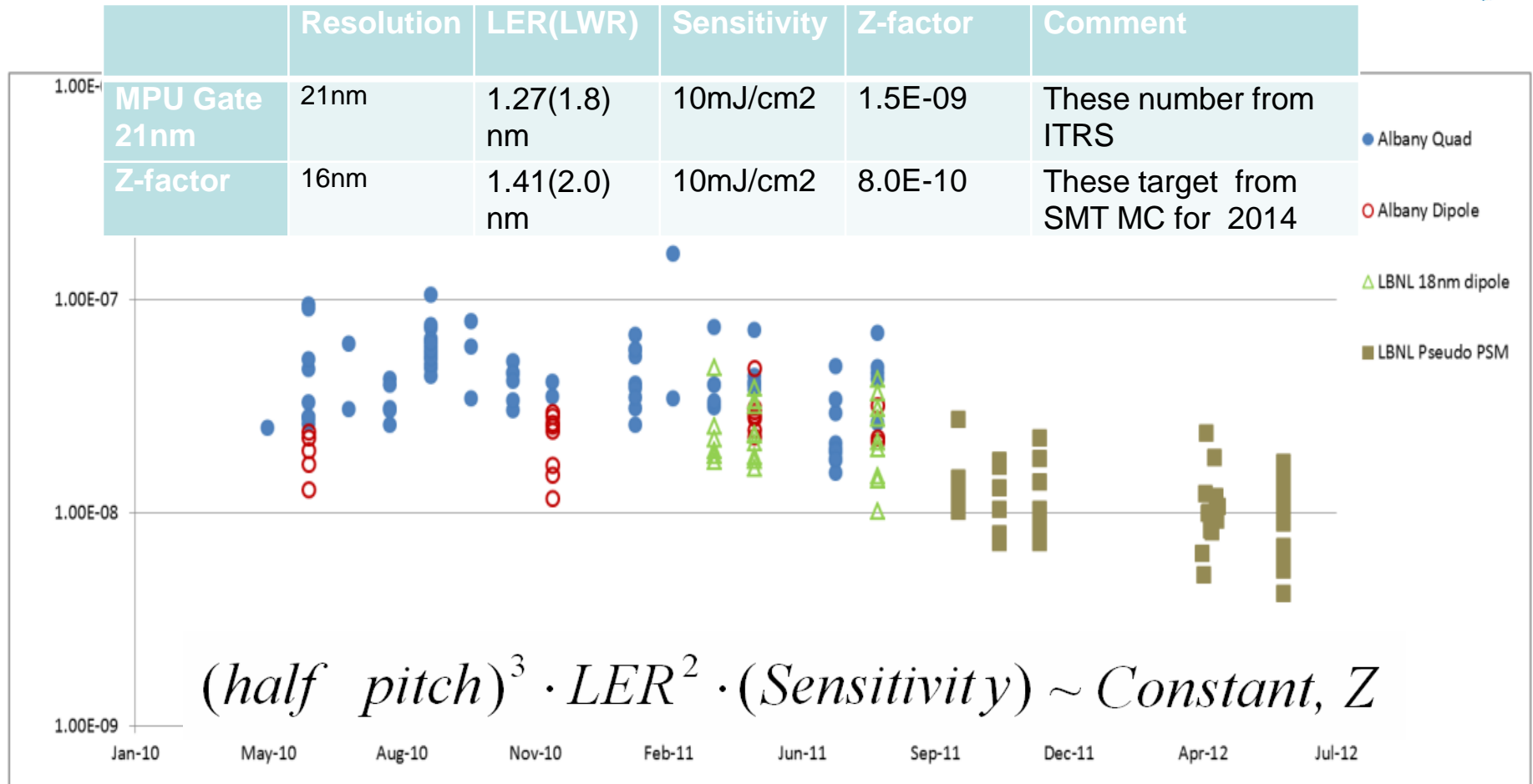
	20nm	19nm	18nm	17nm	16nm	15nm	14nm	13nm
H 33.6mJ	19.3/4.3	18.4/3.5	17.6/3.7	16.4/3.9	15.1/3.7	14.7/3.7	12.5/3.8	
I 46.0mJ	15.2nm/3.9nm	16.2nm/4.2nm	15.8nm/4.1nm	14.9nm/4.0nm	13.1nm/3.6nm	11.6nm/3.2nm	11.3nm/3.5nm	
J 15.6mJ	19.2nm/4.8nm	18.5nm/4.3nm	17.7nm/4.4nm					
K 19.4mJ	19.2/6.2	17.9/4.9	17.1/4.3	15.6/4.9	14.7/4.7			
L 15.5mJ	20.7/4.8	19.6/6.0						
M 15.4mJ	21.1nm/4.2nm	19.9nm/4.5nm	18.3nm/4.8nm					



- Resist H and I showed 15nm resolution.
- Many of suppliers are making progress with patterning performance

Z Value of EUV resists over time

(for lines and spaces)



- Data represents materials from six suppliers
- Improvement in Z value comes from improving the aerial image and material improvements
- Data here is not exactly comparable to ITRS roadmap values due to differences in half pitch and LER measurement details

Oct 2012 Outgas tool status & capacity



	Status	Tested to date	Current Throughput (samples per month)	Total anticipated need based on discussion (per month)
ROX	Up and running	53	8 → 24	
EUVT	August delivery, working towards Q4 certification & customer availability	0	40 - 80	
NIST	Certified Aug/Sept 2011	15 (9 customer samples)	6	
EIDEC	Certification complete, ready to start	0	30 - 40	
IMEC	Recently certified	10	~20	
LTJ	Certified	no data	no data	
Current capacity		78	~70	250, Same as current MET tool capacity
Projected Total Capacity			145	

Meeting Focus

8:00 AM – 8:15 AM	Welcome and Introductions	<i>K. Petrillo, SEMATECH</i>
8:15 AM – 8:35 AM	NIST Outgas Testing Update	<i>S. Hill, NIST</i>
8:35 AM – 8:55 AM	EIDEC Outgas Test Results	<i>T. Takahashi, EIDEC</i>
8:55 AM – 9:15 AM	ROX Outgas Testing Update	<i>G. Denbeaux, CNSE</i>
9:15 AM – 9:35 AM	IMEC Outgas Testing Update	<i>I. Pollentier, IMEC</i>
9:35 AM – 10:05 AM	Break	
10:05 AM – 10:25 AM	EUVT Outgas Testing Update	<i>R. Perera, EUV Technology</i>
10:25 AM – 10:45 AM	DSA as a Mean for EUV Contact Rectification	<i>R. Gronheid, IMEC</i>
10:45 AM – 11:05 AM	DSA as Complementary Lithography: Guiding Pattern Requirements for Contact Shrink and Contact Multiplication	<i>R. Tiron, CEA-Leti</i>
11:05 AM – 11:30 AM	Summary	<i>S. Tedesco, CEA-Leti</i>